

EAST: [10705707.trench buried bit line bbl.wsp:1]

File View Edit Tools Window Help

26) (((b1 bitline bit adj line readline read adj line sense adj line
(2) 6268243.pn.
(562197) capacitor
(52) (((b1 buried adj (b1 bitline bit adj line readline read adj line s
(9) ("4737829" | "4896293" | "5155059" | "5170243" | "52
(4) 5840591.URPN
(3) ("5618745" | "5827092" | "5829228").PN
(4) 5840591.URPN
(52) (((b1 buried adj (b1 bitline bit adj line readline read adj line s
(28) (((b1 bitline bit adj line readline read adj line sense adj line
(74) 5840591.URPN: (((b1 buried adj (b1 bitline bit adj line read
(4577) (spacer liner) near9 (oxide near6 nitride)
(84523) dram
(152) (spacer liner) near9 (oxide near6 nitride) same dram
(7551) cap\$4 near9 nitride
(44) ((spacer liner) near9 (oxide near6 nitride) same dram) and
(7498) bbl (buried trench\$4) adj bit
(12) ((spacer liner) near9 (oxide near6 nitride) same (bbl (buried

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DB: USPAT:US POPUB:EPO:JPO:DERWENT:IDM:TOB

Default operator: QR

Plurals
Highlight all bit terms initially

(((b1 buried adj (b1 bitline bit adj line readline read adj line sense adj line: column)
) and (((b1 bitline bit adj line readline read adj line sense adj line: column)
) near9 trench) same (((b1 bitline bit adj line readline read adj line sense adj line: column)
) near9 (etch\$4: trim\$4))) not micron.as.) and capacitor

June 2004

DRG Item USER Item: Image Test: DR: HSM

	U	Inventor	Document ID	Issue	P	Title	Current	Current XR	Releval	S	C	P	S	S	S	S	Image Doc	P
1	<input checked="" type="checkbox"/>	Park, Jae-Kw	US 5840591 A	1998:1		Method of manufacturing buried bit line	438/262	257/E21.64		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 584059	<input checked="" type="checkbox"/>
2	<input checked="" type="checkbox"/>	Shen, Hua	US 6537870 B1	2003:2		Method of forming an integrated circuit com	438/243	257/E21.65		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 653787	<input checked="" type="checkbox"/>
3	<input checked="" type="checkbox"/>	Athavale, Sat	US 6348374 B1	2002:2		Process for 4F2 STC cell having vertical MO	438/243	257/E21.65		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 634837	<input checked="" type="checkbox"/>
4	<input checked="" type="checkbox"/>	Lee, Robin et	US 6303424 B1	2001:1		Method for fabricating a buried bit line in a D	438/239	257/E21.65		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 630342	<input checked="" type="checkbox"/>
5	<input checked="" type="checkbox"/>	Chen, Min-Lie	US 6271556 B1	2001:1		High density memory structure	257/303	257/301		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 627155	<input checked="" type="checkbox"/>
6	<input checked="" type="checkbox"/>	Lee, Tong-Hsi	US 6127228 A	2000:1		Method of forming buried bit line	438/262	257/E21.50		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 612722	<input checked="" type="checkbox"/>
7	<input checked="" type="checkbox"/>	Lee, Kang-yo	US 5900659 A	1999:1		Buried bit line DRAM cells	257/296	257/306		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 590065	<input checked="" type="checkbox"/>
8	<input checked="" type="checkbox"/>	Beer, Peter	US 20030011010	2003:0		Integrated semiconductor memory and fabric	257/296			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200300	<input checked="" type="checkbox"/>
9	<input checked="" type="checkbox"/>	Divakaruni, R	US 20030001200	2003:0		Modified vertical MOSFET and methods of fo	257/330	257/332		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200300	<input checked="" type="checkbox"/>
10	<input checked="" type="checkbox"/>	Asano, Isamu	US 20020155662	2002:1		Method of manufacturing a semiconductor in	438/253	257/E21.64		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200201	<input checked="" type="checkbox"/>
11	<input checked="" type="checkbox"/>	HIEDA, KATS	US 20020153552	2002:1		SEMICONDUCTOR DEVICE AND METHOD FO	257/308	257/E21.00		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200201	<input checked="" type="checkbox"/>
12	<input checked="" type="checkbox"/>	Athavale, Sat	US 20020130346	2002:0		Structure and process for buried bitline and s	257/301	257/E21.65		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200201	<input checked="" type="checkbox"/>
13	<input checked="" type="checkbox"/>	Lee, Thomas	US 20020026541	2002:0		Dense arrays and charge storage devices, an	438/149	257/E27.02		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200200	<input checked="" type="checkbox"/>
14	<input checked="" type="checkbox"/>	Economikos, US	20010017394	2001:0		Method of forming a buried bitline in a vertic	257/302	257/E21.85		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200100	<input checked="" type="checkbox"/>
15	<input checked="" type="checkbox"/>	Asano, Isamu	US 6696337 B2	2004:6		Method of manufacturing a semiconductor in	438/253	438/241		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 669633	<input checked="" type="checkbox"/>
16	<input checked="" type="checkbox"/>	Alsmeyer, Joh	US 6593813 B1	2003:0		Memory cell for plateline sensing	257/308	257/298		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 659381	<input checked="" type="checkbox"/>
17	<input checked="" type="checkbox"/>	Athavale, Sat	US 6518118 B2	2003:0		Structure and process for buried bitline and s	438/243	257/E21.65		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 651811	<input checked="" type="checkbox"/>
18	<input checked="" type="checkbox"/>	Furukawa, T	US 6440801 B1	2002:7		Structure for folded architecture pillar mem	438/272	257/302		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 644080	<input checked="" type="checkbox"/>